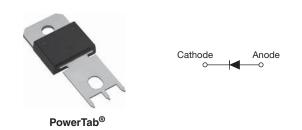


Ultrafast Soft Recovery Diode, 80 A FRED Pt®



PRODUCT SUMMARY				
Package PowerTab [®]				
I _{F(AV)}	80 A			
V_{R}	400 V			
V _F at I _F	1.3 V			
t _{rr} (typ.)	See recovery table			
T _J max.	175 °C			
Diode variation	Single die			

FEATURES

- Ultrafast recovery time
- 175 °C max. operating junction temperature
- Screw mounting only
- Designed and qualified according to JEDEC-JESD47



PowerTab[®] package





COMPLIANT

BENEFITS

- Reduced RFI and EMI
- · Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION/APPLICATIONS

These diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems.

The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for HF welding, power converters and other applications where switching losses are not significant portion of the total losses.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS		UNITS	
Cathode to anode voltage	V _R		400	V	
Continuous forward current	I _{F(AV)}	T _C = 101 °C	80		
Single pulse forward current	I _{FSM}	T _C = 25 °C	800	Α	
Maximum repetitive forward current	I _{FRM}	Square wave, 20 kHz	160		
Operating junction and storage temperatures	T _J , T _{Stg}		- 55 to 175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS		TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V _{BR} , V _r	I _R = 100 μA		-	-	
		I _F = 80 A	-	1.1	1.3	V
Forward voltage	V_{F}	I _F = 80 A, T _J = 175 °C	-	0.92	1.08	
		I _F = 80 A, T _J = 125 °C		0.98	1.15	
Poverse leeke ge ourrent	_	V _R = V _R rated	-	-	50	μΑ
Reverse leakage current I _R	I _R	$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	-	2	mA
Junction capacitance	C _T	V _R = 200 V	-	50	-	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body - 3.5 -		nH		



DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	50	60	
Reverse recovery time t _{rr}	T _J = 25 °C		-	87	-	ns	
		T _J = 125 °C	I _F = 80 A V _R = 200 V dI _F /dt = 200 A/μs	-	151	-	
Peak recovery current	I _{RRM}	T _J = 25 °C		-	9.3	-	- А
		T _J = 125 °C		-	17.2	-	
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	405	-	- nC
		T _J = 125 °C		-	1300	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction to case	R _{thJC}		-	-	0.70	K/W
Thermal resistance, junction to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.2	-	N/VV
Weight			-	-	5.02	g
vveigni			-	0.18	-	oz.
Mounting torque			1.2 (10)	-	2.4 (20)	N · m (lbf · in)
Marking device		Case style PowerTab®	80EBU04			

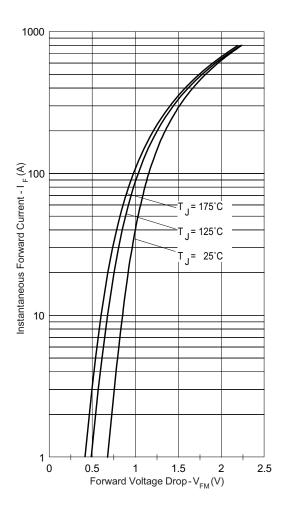


Fig. 1 - Maximum Forward Voltage Drop Characteristics

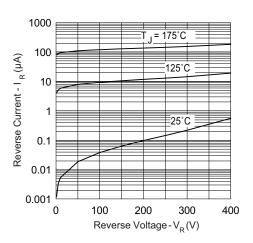


Fig. 1 - Typical Values of Reverse Current vs. Reverse Voltage

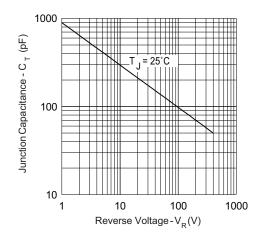


Fig. 2 - Typical Junction Capacitance vs. Reverse Voltage

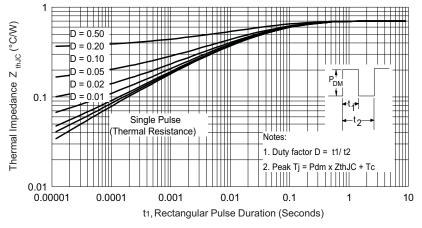


Fig. 3 - Maximum Thermal Impedance Z_{thJC} Characteristics



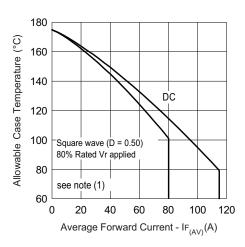


Fig. 2 - Maximum Allowable Case Temperature vs.
Average Forward Current

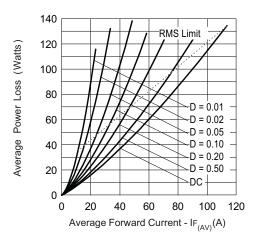


Fig. 4 - Forward Power Loss Characteristics

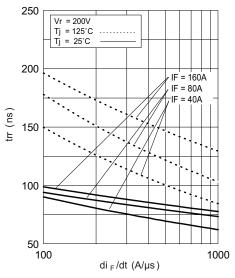


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

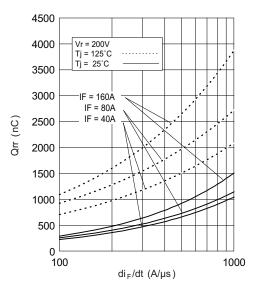


Fig. 6 - Typical Stored Charge vs. dl_F/dt

Note

 $^{(1)}$ Formula used: T_C = T_J - (Pd + Pd_{REV}) x R_{th,JC}; Pd = Forward power loss = I_{F(AV)} x V_{FM} at (I_{F(AV)}/D) (see fig. 6); Pd_{REV} = Inverse power loss = V_{R1} x I_R (1 - D); I_R at V_{R1} = 80 % rated V_R

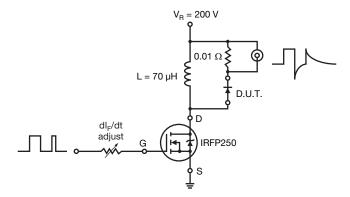
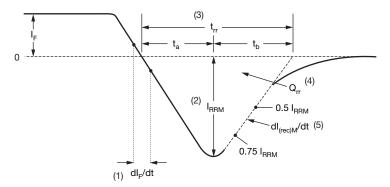


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

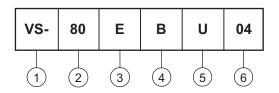
(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (80 = 80 A)

3 - Single diode

PowerTab[®] (ultrafast/hyperfast only)

5 - Ultrafast recovery

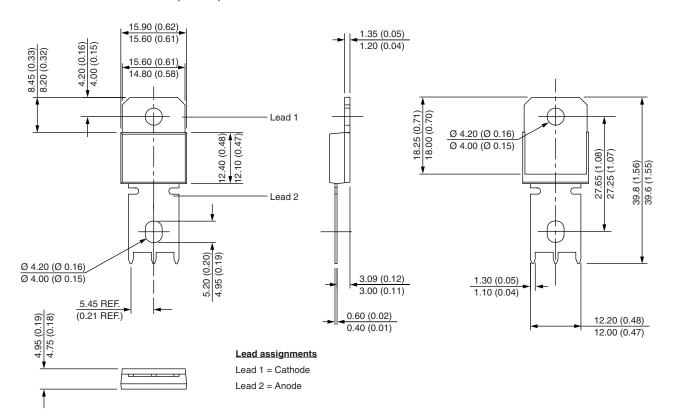
6 - Voltage rating (04 = 400 V)

LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95240</u>					
Part marking information <u>www.vishay.com/doc?95370</u>					
Application note	www.vishay.com/doc?95179				



PowerTab®

DIMENSIONS in millimeters (inches)







Vishay

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